

UDE

SOD-123 Plastic-Encapsulate Diodes

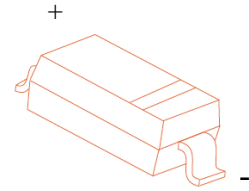
SD103AW-SD103CW SCHOTTKY DIODES

FEATURES

- Low forward voltage drop
- Guard ring construction for transient protection
- Negligible reverse recovery time
- Low reverse capacitance

MARKING: SD103AW: S4
SD103BW: S5
SD103CW: S6

SOD-123



Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Peak Repetitive Peak reverse voltage	V_{RRM}				
Working Peak	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Repetitive Peak Forward Current @ $t \leq 1.0\text{s}$	I_{FRM}	1.5			A
Power Dissipation	P_d	500			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	250			$^\circ\text{C/W}$
Storage temperature	T_{STG}	-65~+150			$^\circ\text{C}$

Electrical Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	SD103AW SD103BW SD103CW	40 30 20			V	$I_R=100\mu\text{A}$ $I_R=100\mu\text{A}$ $I_R=100\mu\text{A}$
Forward voltage	V_F			0.37 0.60	V	$I_F=20\text{mA}$ $I_F=200\text{mA}$
Reverse current	SD103AW SD103BW SD103CW			5.0	μA	$V_R=30\text{V}$ $V_R=20\text{V}$ $V_R=10\text{V}$
Capacitance between terminals	C_T		50		pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}		10		ns	$I_F=I_R=200\text{mA}$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$

Typical Characteristics

SD103AW-SD103CW

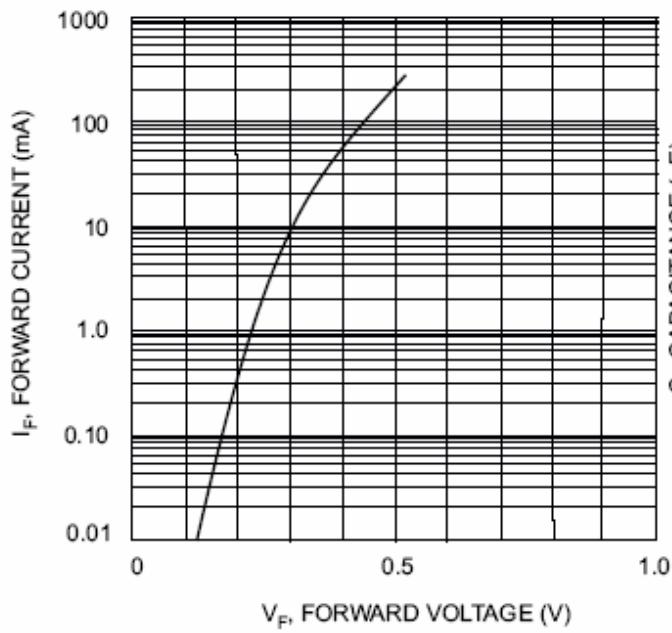


Fig. 1 Typical Forward Characteristics

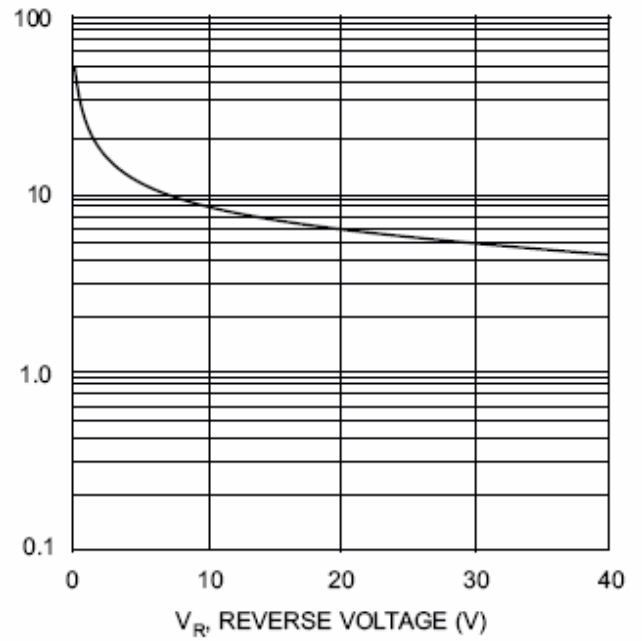


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage